

## SERIAL NO.

## Unknown

HERBERT et al.

**GROUP**

(Use several sheets if necessary)

Herewith

[illegible]

FOUR-LEVEL DOCUMENTS							TRANSLATION	
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO	
<i>DHIL</i>	0 262 346	04/1988	EP			/		
<i>DHIL</i>	2 002 579	02/1979	GB			/		
<i>DHIL</i>	0 757 392	02/1997	EP			/		
			/			/		

h h u	MISHRA J K et al.: "Design optimization of a Single-sided SI/SIGE heterostructure mixed tunnelling avalanche transit time double drift region" Semiconductor Science and Technology, GB, Institute of Physics, London, vol. 12, no. 12, pp. 1635-1640
h h u	MISHRA J K et al.: "An extremely low noise heterojunction impatt" IEEE transactions on electron devices, US, IEEE INC. New York, vol. 44, no. 12, pp. 2143-2148
h h u	KEARNEY M. J.: "Heterojunction impact avalanche transit time diodes grown by molecular beam epitaxy" Semiconductor Science and Technology, GB, Institute of Physics. London, vol. 8, no. 4, pp. 560-567

8-21-02

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